#### TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

# 2SD2539

# HORIZONTAL DEFLECTION OUTPUT FOR COLOR TVs

Unit: mm

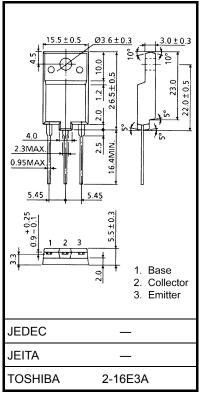
 $\begin{array}{ll} \bullet & \mbox{High Voltage} & : \mbox{V}_{\mbox{CBO}} = 1500 \ \mbox{V} \\ \bullet & \mbox{Low Saturation Voltage} & : \mbox{V}_{\mbox{CE (sat)}} = 5 \ \mbox{V (Max.)} \\ \bullet & \mbox{High Speed} & : \mbox{t}_{\mbox{f}} = 0.3 \ \mbox{\mus (Typ.)} \\ \end{array}$ 

• Built-in Damper Type

• Collector Metal (Fin) is Fully Covered with Mold Resin

### **ABSOLUTE MAXIMUM RATINGS (Tc = 25°C)**

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		$V_{CBO}$	1500	V	
Collector-Emitter Voltage		V <sub>CEO</sub>	600	V	
Emitter-Base Voltage		V <sub>EBO</sub>	5	V	
Collector Current	DC	IC	7	Α	
	Pulse	I <sub>CP</sub>	14		
Base Current		ΙB	3.5	Α	
Collector Power Dissipation		PC	50	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T <sub>stg</sub>	-55~150	°C	



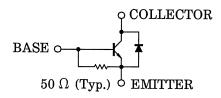
Weight: 5.5 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

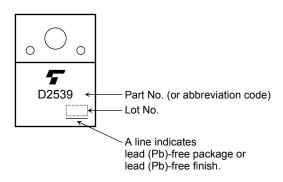
temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **EQUIVALENT CIRCUIT**



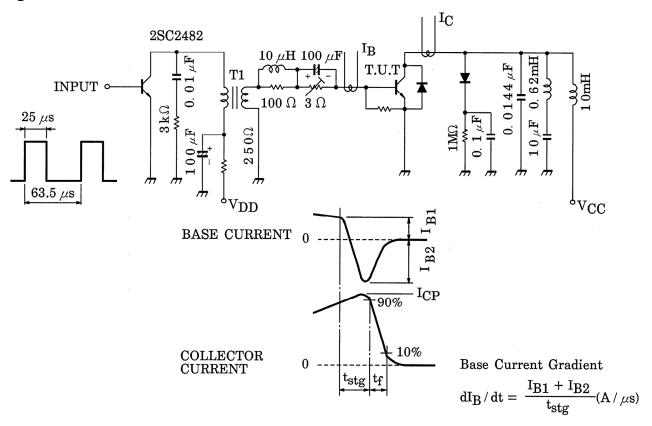
#### **MARKING**

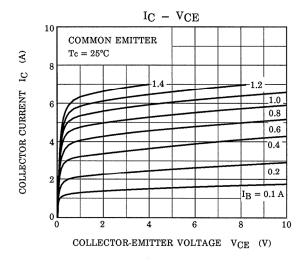


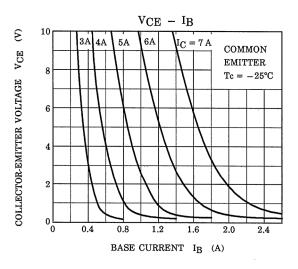
## **ELECTRICAL CHARACTERISTICS (Tc = 25°C)**

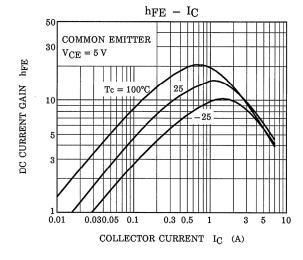
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current		I <sub>CBO</sub>	V <sub>CB</sub> = 1500 V, I <sub>E</sub> = 0	_	_	1	mA
Emitter Cut-off Current		I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	66	_	200	mA
Emitter-Base Breakdown Voltage		V (BR) EBO	I <sub>C</sub> = 400 mA, I <sub>B</sub> = 0	5	_	_	V
DC Current Gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1 A	8	_	28	_
		h <sub>FE</sub> (2)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 5A	5	_	9	
Collector-Emitter Saturation Voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 5 A, I <sub>B</sub> = 1.0 A	_	_	5	V
Base-Emitter Saturation Voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = 5 A, I <sub>B</sub> = 1.0 A	_	1.0	1.3	V
Forward Voltage (Damper Diode)		V <sub>F</sub>	I <sub>F</sub> = 5 A	_	1.6	2.0	٧
Transition Frequency		f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 0.1 A	_	2	_	MHz
Collector Output Capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	115	_	pF
Switching Time	Storage Time	t <sub>stg</sub>	I <sub>CP</sub> = 5 A, I <sub>B1</sub> (end) = 1.0 A f <sub>H</sub> = 15.75 kHz	_	6	9	μs
	Fall Time	t <sub>f</sub>		_	0.3	0.6	

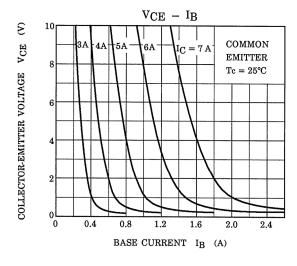
Fig.1 SWITCHING TIME TEST CIRCUIT

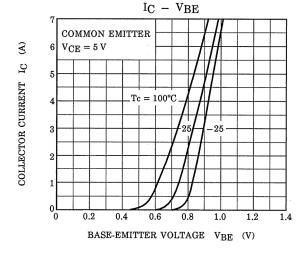


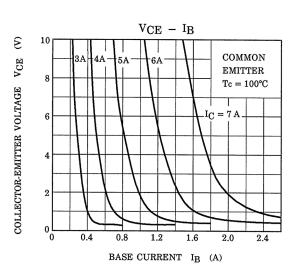


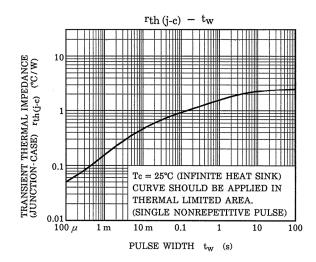


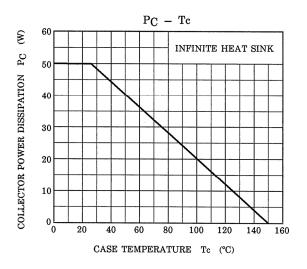


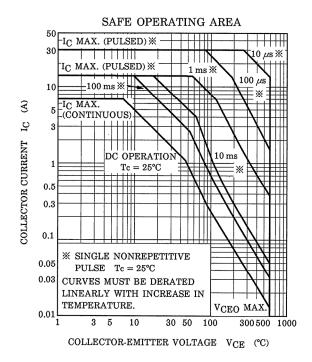












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